



Atty. Dkt. No. 029437-0108

IFW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yasuhiro OKAMOTO et al.
Title: FIELD-EFFECT TRANSISTOR HAVING GROUP III NITRIDE
ELECTRODE STRUCTURE
Appl. No.: 10/538,739
Filing Date: 11/9/2005
Examiner: Salerno, Sarah Kate
Art Unit: 2814
Confirmation No.: 7288

AMENDMENT AND REPLY UNDER 37 C.F.R. 1.111

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

This communication is responsive to the Non-Final Office Action dated June 21, 2010, concerning the above-referenced patent application.

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this document.

Remarks/Arguments begin on page 8 of this document.

Please amend the application as follows: